MGBR40V200C

# DUAL MOS GATED BARRIER RECTIFIER

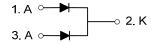
#### **■** DESCRIPTION

The UTC **MGBR40V200C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

#### ■ FEATURES

- \* Very low forward voltage drop
- \* High switching speed

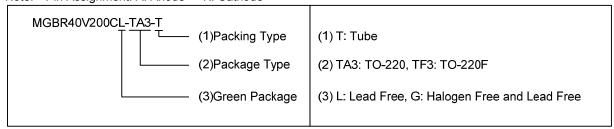
### ■ SYMBOL



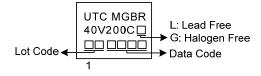
# ■ ORDERING INFORMATION

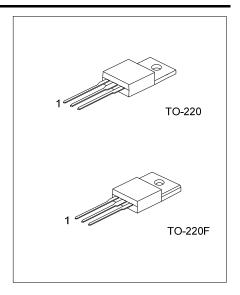
Ordering Number		Dackago	Pin Assignment			Packing	
Lead Free	Halogen Free	Package	1	2	3	Facking	
MGBR40V200CL-TA3-T MGBR40V200CG-T		TO-220	Α	K	Α	Tube	
MGBR40V200CL-TF3-T	MGBR40V200CG-TF3-T	TO-220F	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Cathode



## **■ MARKING**





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MGBR40V200C DIODE

# ■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T<sub>A</sub>=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		$V_{RM}$	200	V
Working Peak Reverse Voltage		$V_{RWM}$	200	V
Peak Repetitive Reverse Voltage		$V_{RRM}$	200	V
Average Rectified Output Current Per Device	Per Leg	l <sub>o</sub>	20	Α
	Total		40	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I <sub>FSM</sub>	240	Α
Operating Junction Temperature		$T_J$	-65 ~ +150	°C
Storage Temperature		$T_{STG}$	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL CHARACTERISTICS (PER LEG)**

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient		$\theta_{JA}$	62.5	°C/W	
Tunation to Cook	ΓΟ-220	0	2	°C/M	
Junction to Case	ΓO-220F	$\theta$ <sub>JC</sub>	3.31	°C/W	

## ■ **ELECTRICAL CHARACTERISTICS (PER LEG)** (T<sub>A</sub> =25°C unless otherwise specified.)

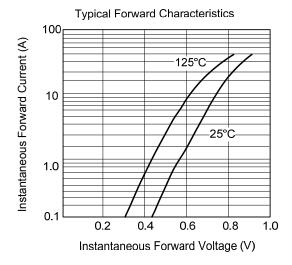
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I <sub>R</sub> =0.50mA	200			V
Famurad Valtage Dran	V-14	I <sub>F</sub> =20A, T <sub>J</sub> =25°C			0.89	V
Forward Voltage Drop		I <sub>F</sub> =20A, T <sub>J</sub> =125°C			0.73	V
Lookana Cumant (Note 4)	lьм	V <sub>R</sub> =200V, T <sub>J</sub> =25°C			200	μΑ
Leakage Current (Note 1)		V <sub>R</sub> =200V, T <sub>J</sub> =125°C			40	mA

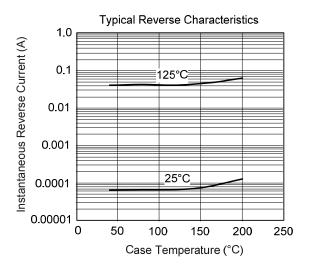
Notes: 1. Short duration pulse test used to minimize self-heating effect.

<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

MGBR40V200C DIODE

## TYPICAL CHARACTERISTICS





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